

**isc Silicon NPN Darlington Power Transistor**
**2SD1893**
**DESCRIPTION**

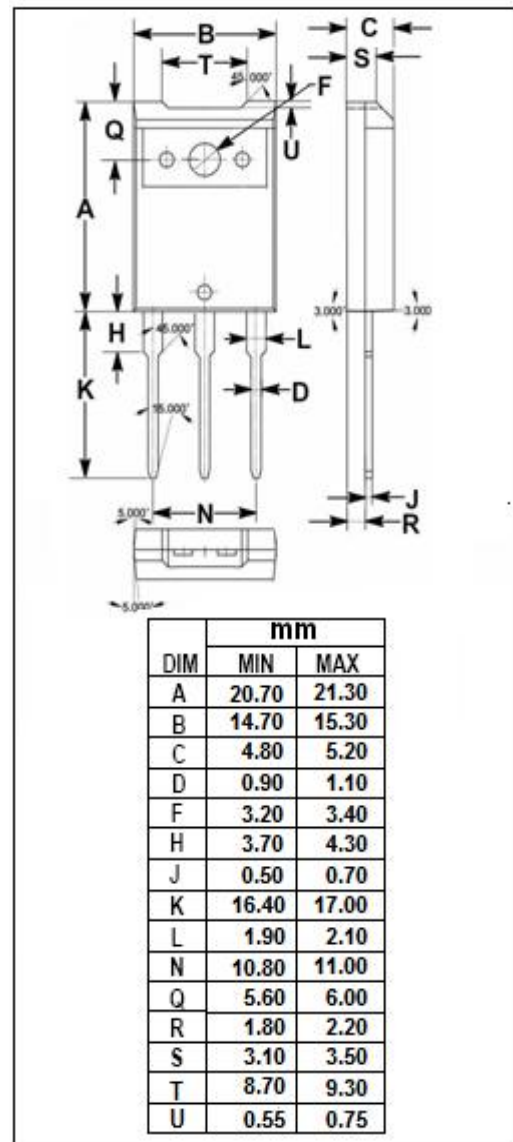
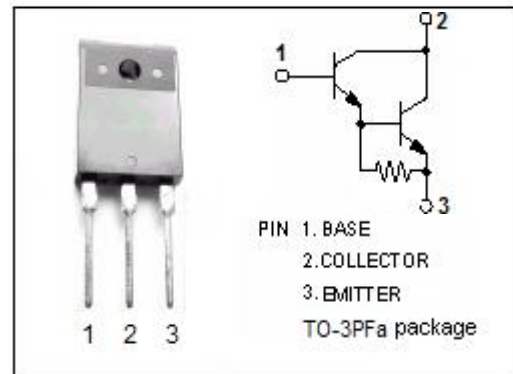
- High DC Current Gain-  
:  $h_{FE} = 5000(\text{Min})@I_C = 5A$
- Low-Collector Saturation Voltage-  
:  $V_{CE(\text{sat})} = 2.5V(\text{Max.})@I_C = 5A$
- Complement to Type 2SB1253
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for power amplifier applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	130	V
$V_{CEO}$	Collector-Emitter Voltage	110	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	6	A
$I_{CM}$	Collector Current-Peak	10	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	50	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	110			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 5mA			2.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 5mA			3.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 130V; I <sub>E</sub> = 0			100	μ A
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 110V; I <sub>B</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	2000			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	5000		30000	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		20		MHz

**Switching Times**

t <sub>on</sub>	Turn-on Time			1.4		μ s
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = I <sub>B2</sub> = 5mA, V <sub>CC</sub> = 50V		4.5		μ s
t <sub>f</sub>	Fall Time			0.8		μ s

**◆ h<sub>FE-2</sub> Classifications**

Q	P
5000-15000	8000-30000

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